

# DMG564H3

Silicon NPN epitaxial planar type (Tr1)  
 Silicon PNP epitaxial planar type (Tr2)

For digital circuits

## ■ Features

- Low collector-emitter saturation voltage  $V_{CE(sat)}$
- Halogen-free / RoHS compliant  
 (EU RoHS / UL-94 V-0 / MSL: Level 1 compliant)

## ■ Marking Symbol: T4

## ■ Basic Part Number

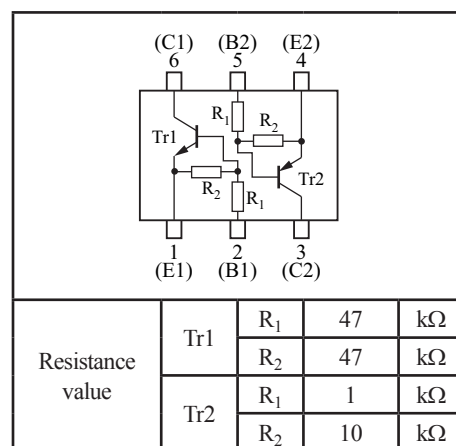
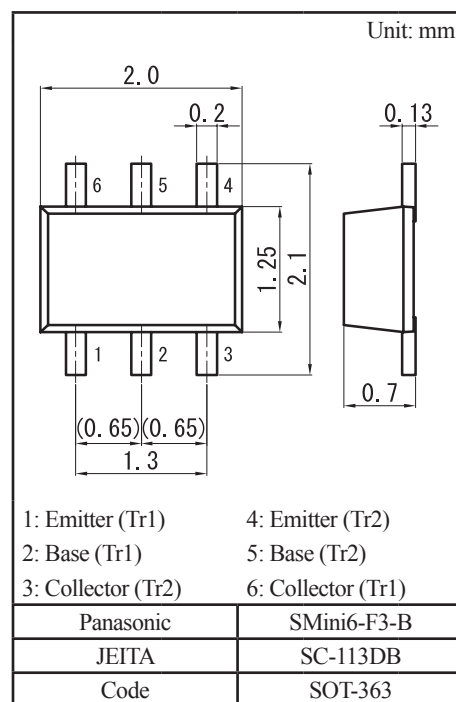
DRC2144E + DRA2113Z (Individual)

## ■ Packaging

DMG564H30R Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

## ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter		Symbol	Rating	Unit
Tr1	Collector-base voltage (Emitter open)	$V_{CBO}$	50	V
	Collector-emitter voltage (Base open)	$V_{CEO}$	50	V
	Collector current	$I_C$	100	mA
Tr2	Collector-base voltage (Emitter open)	$V_{CBO}$	-50	V
	Collector-emitter voltage (Base open)	$V_{CEO}$	-50	V
	Collector current	$I_C$	-100	mA
Overall	Total power dissipation	$P_T$	150	mW
	Junction temperature	$T_j$	150	$^\circ\text{C}$
	Operating ambient temperature	$T_{opr}$	-40 to +85	$^\circ\text{C}$
	Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$



■ Electrical Characteristics  $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

• Tr1

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{\text{CBO}}$	$I_{\text{C}} = 10 \mu\text{A}, I_{\text{E}} = 0$	50			V
Collector-emitter voltage (Base open)	$V_{\text{CEO}}$	$I_{\text{C}} = 2 \text{mA}, I_{\text{B}} = 0$	50			V
Collector-base cutoff current (Emitter open)	$I_{\text{CBO}}$	$V_{\text{CB}} = 50 \text{V}, I_{\text{E}} = 0$			0.1	$\mu\text{A}$
Collector-emitter cutoff current (Base open)	$I_{\text{CEO}}$	$V_{\text{CE}} = 50 \text{V}, I_{\text{B}} = 0$			0.5	$\mu\text{A}$
Emitter-base cutoff current (Collector open)	$I_{\text{EBO}}$	$V_{\text{EB}} = 6 \text{V}, I_{\text{C}} = 0$			0.1	mA
Forward current transfer ratio	$h_{\text{FE}}$	$V_{\text{CE}} = 10 \text{V}, I_{\text{C}} = 5 \text{mA}$	80			—
Collector-emitter saturation voltage	$V_{\text{CE(sat)}}$	$I_{\text{C}} = 10 \text{mA}, I_{\text{B}} = 0.5 \text{mA}$			0.25	V
Input voltage (ON)	$V_{\text{I(on)}}$	$V_{\text{CE}} = 0.2 \text{V}, I_{\text{C}} = 5 \text{mA}$	3.6			V
Input voltage (OFF)	$V_{\text{I(off)}}$	$V_{\text{CE}} = 5 \text{V}, I_{\text{C}} = 100 \mu\text{A}$			0.8	V
Input resistance	$R_1$		-30%	47	+30%	$\text{k}\Omega$
Resistance ratio	$R_1 / R_2$		0.8	1.0	1.2	—

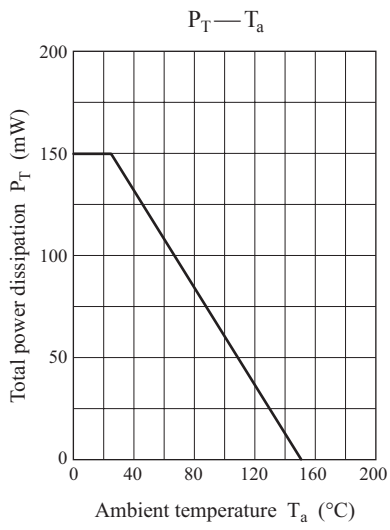
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

• Tr2

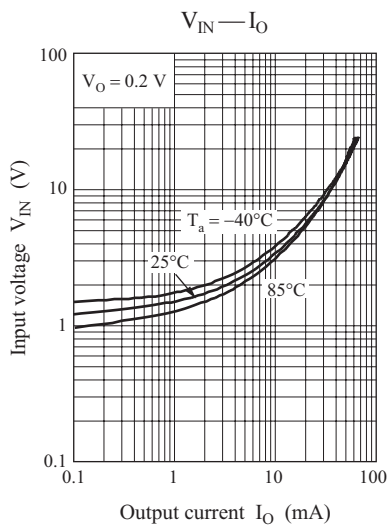
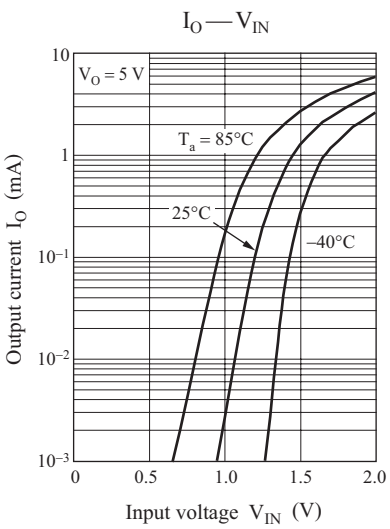
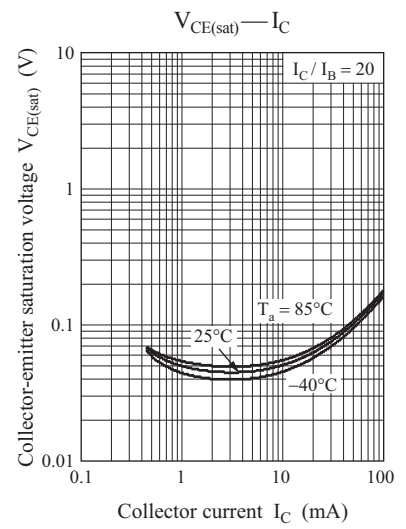
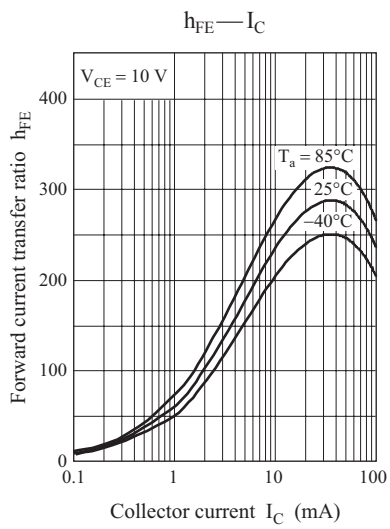
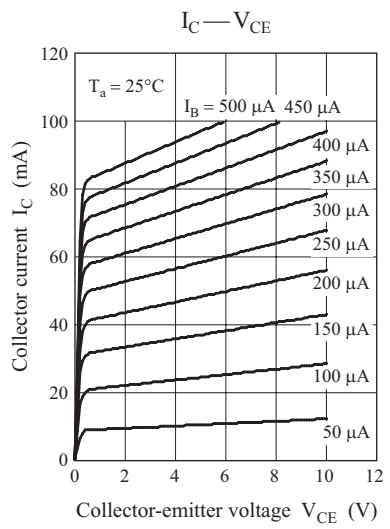
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{\text{CBO}}$	$I_{\text{C}} = -10 \mu\text{A}, I_{\text{E}} = 0$	-50			V
Collector-emitter voltage (Base open)	$V_{\text{CEO}}$	$I_{\text{C}} = -2 \text{mA}, I_{\text{B}} = 0$	-50			V
Collector-base cutoff current (Emitter open)	$I_{\text{CBO}}$	$V_{\text{CB}} = -50 \text{V}, I_{\text{E}} = 0$			-0.1	$\mu\text{A}$
Collector-emitter cutoff current (Base open)	$I_{\text{CEO}}$	$V_{\text{CE}} = -50 \text{V}, I_{\text{B}} = 0$			-0.5	$\mu\text{A}$
Emitter-base cutoff current (Collector open)	$I_{\text{EBO}}$	$V_{\text{EB}} = -6 \text{V}, I_{\text{C}} = 0$			-1.5	mA
Forward current transfer ratio	$h_{\text{FE}}$	$V_{\text{CE}} = -10 \text{V}, I_{\text{C}} = -5 \text{mA}$	30			—
Collector-emitter saturation voltage	$V_{\text{CE(sat)}}$	$I_{\text{C}} = -10 \text{mA}, I_{\text{B}} = -0.5 \text{mA}$			-0.25	V
Input voltage (ON)	$V_{\text{I(on)}}$	$V_{\text{CE}} = -0.2 \text{V}, I_{\text{C}} = -5 \text{mA}$	-1.0			V
Input voltage (OFF)	$V_{\text{I(off)}}$	$V_{\text{CE}} = -5 \text{V}, I_{\text{C}} = -100 \mu\text{A}$			-0.4	V
Input resistance	$R_1$		-30%	1	+30%	$\text{k}\Omega$
Resistance ratio	$R_1 / R_2$		0.08	0.10	0.12	—

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

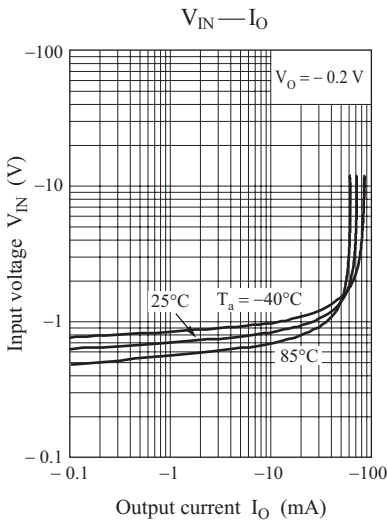
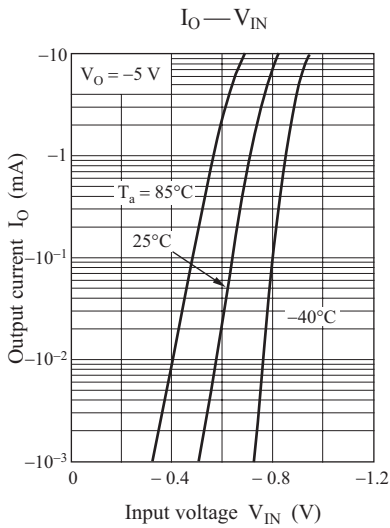
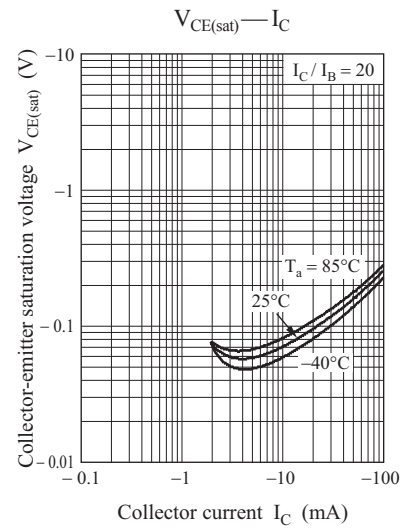
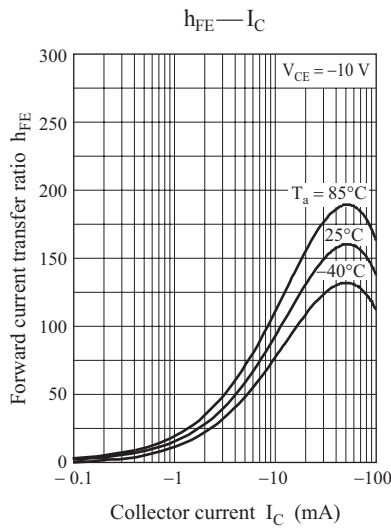
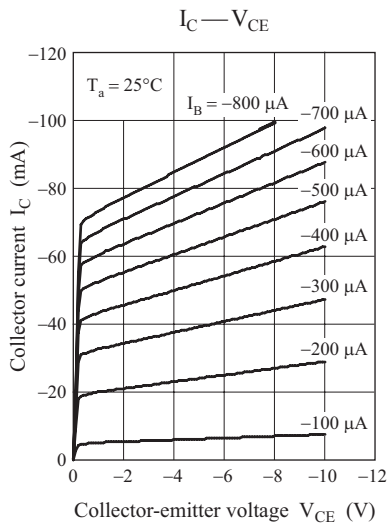
Common characteristics chart



Characteristics charts of Tr1

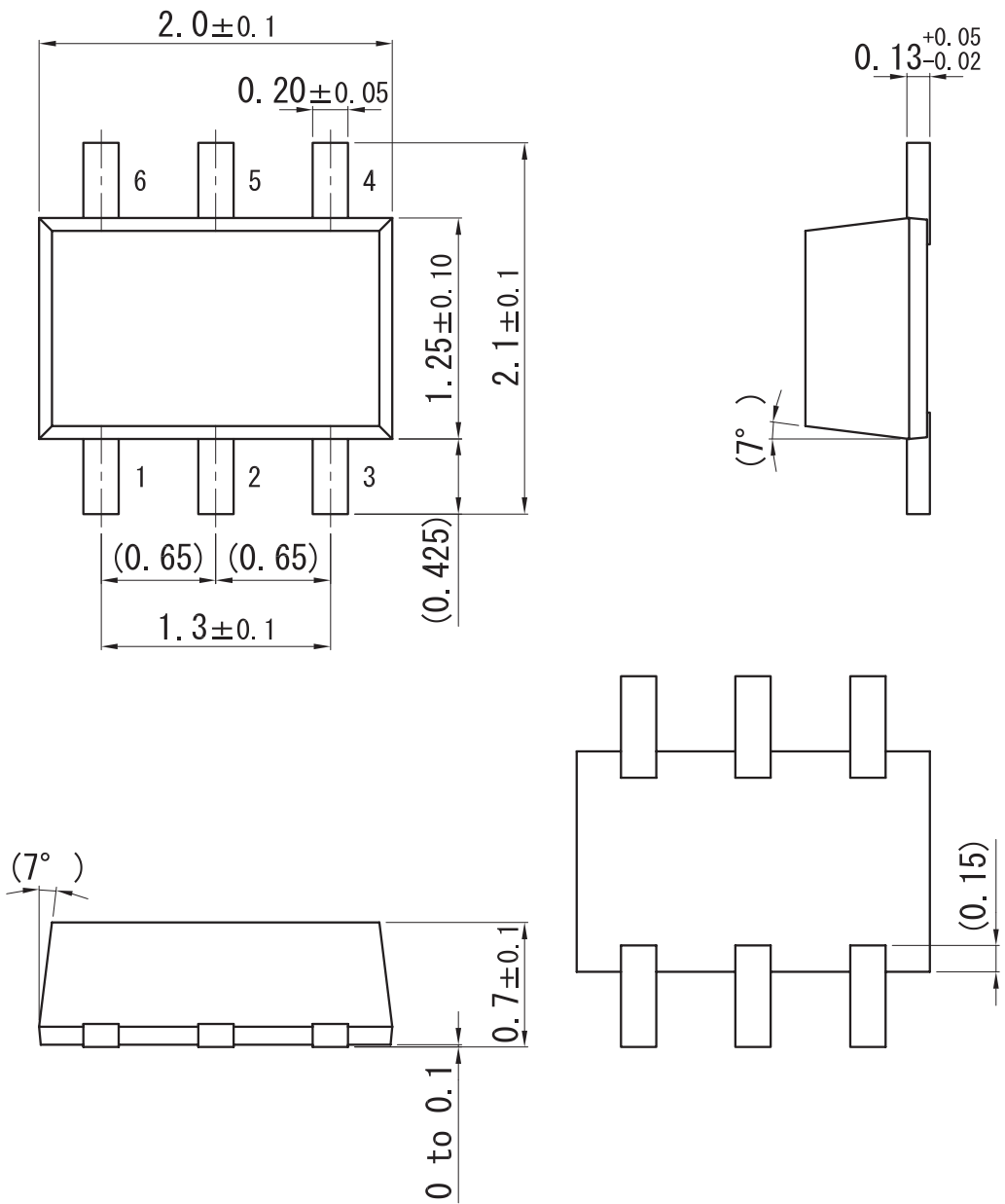


Characteristics charts of Tr2

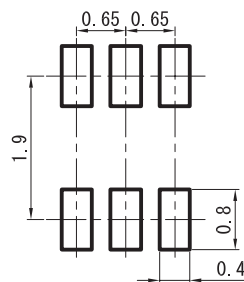


SMini6-F3-B

Unit: mm



■ Land Pattern (Reference) (Unit: mm)



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